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Poster Presentation

## [AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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10:40 AM - 1:10 PM

## [AMDp1-8]Characteristics of Top-gate Self-aligned Oxide A-IGZO TFT With Copper Light Shield Layer

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Keywords:Top-gate Self-aligned, a-IGZO TFTs, Short channel TFT, stability

*A top-gate self-aligned oxide amorphous indium-gallium-zinc-oxide (a-IGZO) thin-film transistor (TFT) was examined for active matrix organic light-emitting diode (AMOLED) display. The device exhibited robust device performance, such as excellent threshold voltage uniformity, high mobility, and good gate bias stress stabilities. Furthermore, remarkable short channel characteristics were achieved.*